

Appl. No. 10/605,585
Response dated August 24, 2005
Reply to Office Action mailed May 24, 2005

The following listing of claims will replace all prior versions, and listings, of claims in the application.

LISTING OF CLAIMS:

Claim 1 (currently amended): A semiconductor device, comprising:
a unitary and non-layered semiconductor substrate comprising a thin portion that is thinner than adjacent portions of the semiconductor substrate, and a recessed portion formed below the thin portion; main unit; and
~~a thin portion that is thinner than the main unit and formed such that a recessed portion is formed in the semiconductor substrate, the thin portion having at least one through hole formed therein;~~
wherein the ~~main unit and the thin portion are comprised of the same semiconductor material; and~~
wherein the etching rate of the thin portion is formed such that the etching rate thereof is slower than that of the surrounding portions of the semiconductor substrate main unit; and
at least one through hole is formed in the thin portion that extends from the recessed portion, and entirely through the thin portion to the upper surface of the thin portion.

Claim 2 (cancelled)

Claim 3 (original): The semiconductor device set forth in claim 1, wherein a dopant is infused in the thin portion.

Claim 4 (original): The semiconductor device set forth in claim 1, wherein the thin portion is formed by means of a selective oxide film.

Claims 5-12 (cancelled)